

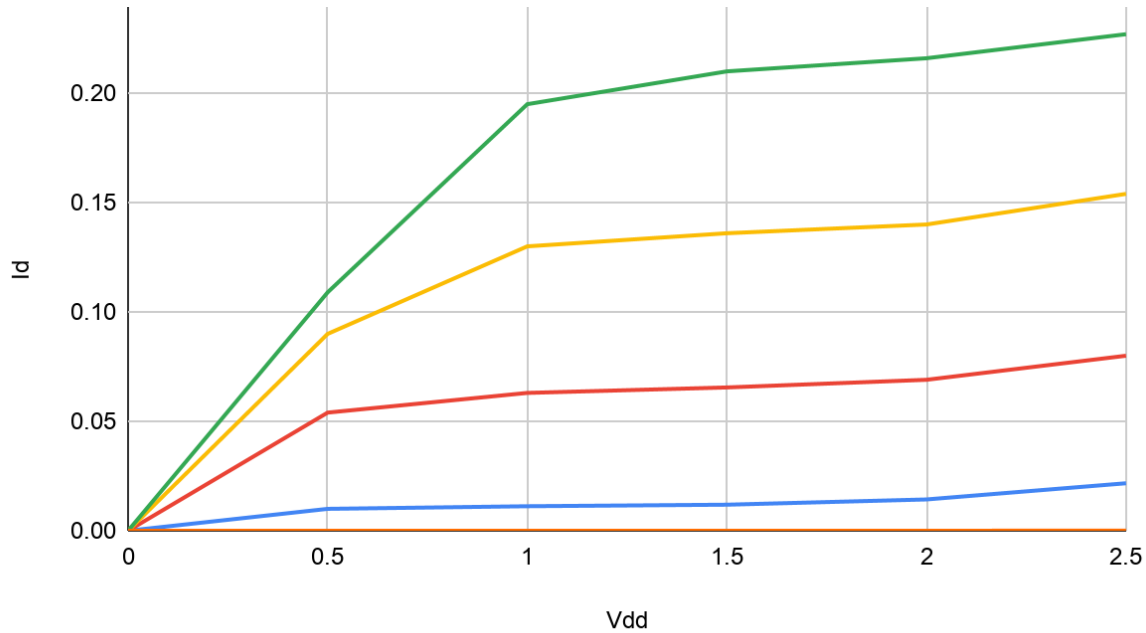
EE330 Lab 7
Section 5, 8:00 am

MOSFET Device Experimental
Characterization and Basic Applications

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Part 2. Measurement of MOSFET output characteristics

For this section I chose not to use signal express, as it had recently been updated and there were no recent guides created. Instead, I hooked the transistor chip up to a breadboard and, using several voltage supplies and an ammeter, collected 30 data points represented by the graph below:

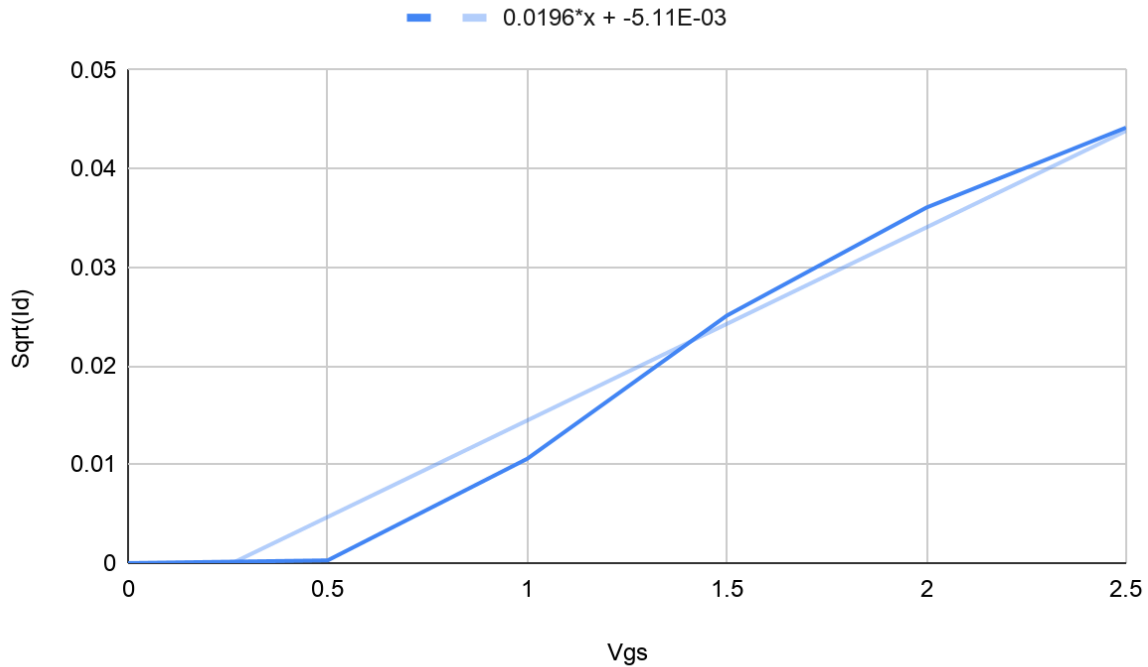


This data was collected by varying V_{dd} and V_{gs} in sequence, covering the range of V_{dd} : $0 \rightarrow 2.5$, and V_{gs} : $0.5 \rightarrow 2.5$

| | Vg | 0.5 | 1 | 1.5 | 2 | 2.5 |
|-----|----|------|------|------|-------|-------|
| Vdd | | | | | | |
| 0 | | 0 | 0 | 0 | 0 | 0 |
| 0.5 | | 60n | 100u | 540u | 900u | 1.09m |
| 1 | | 76n | 112u | 630u | 1.3m | 1.95m |
| 1.5 | | 92n | 119u | 655u | 1.36m | 2.1m |
| 2 | | 108n | 143u | 690u | 1.4m | 2.16m |
| 2.5 | | 125n | 217u | 800u | 1.54m | 2.27m |

Part 3. Measurement of MOSFET parameters

As $I_D = \frac{\mu_{Cox} * W}{2 * L} (V_{GS} - V_{T0})^2$, then $\sqrt{I_D} = \sqrt{\frac{\mu_{Cox} * W}{2 * L}} (V_{GS} - V_{T0})$, where $\sqrt{\frac{\mu_{Cox} * W}{2 * L}}$ is the slope of the line. Therefore, finding the slope of the I_D curve when holding V_{DD} constant and varying V_{GS} will allow us to find μ_{Cox} :



| | |
|-----|----------------|
| 0 | 0 |
| 0.5 | 0.000275680975 |
| 1 | 0.01058300524 |
| 1.5 | 0.0250998008 |
| 2 | 0.03605551275 |
| 2.5 | 0.04415880433 |

Measuring μ_{Cox} :

I have no idea what the size of this transistor is, so I'm going to assume $W/L = 5$.

Then, as slope = .0196, **$\mu_{Cox} = 154 \text{ uA/V}^2$**

This is very close to the typical value of 150 uA/V^2

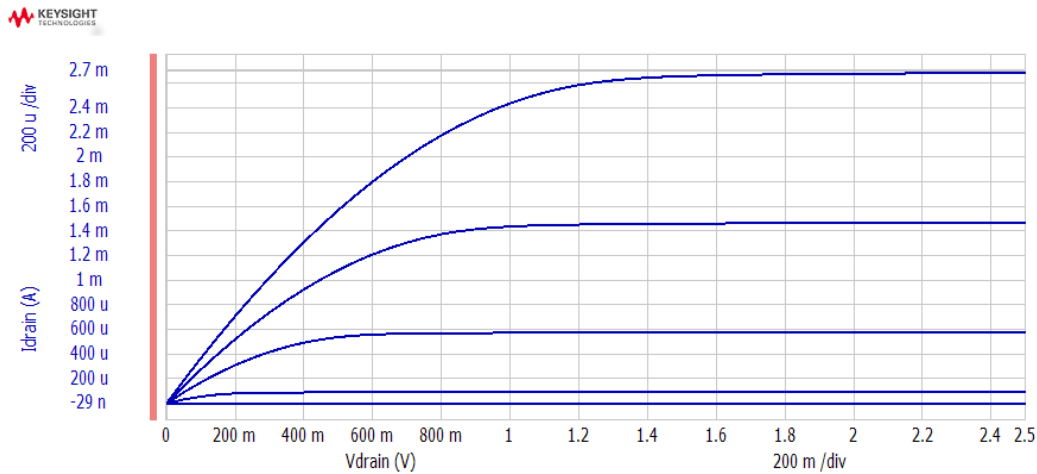
Measuring γ :

No time. It's probably ~ 0.6 .

Measuring λ :

I'd really rather not. Also probably around 0.015.

Part 4. Measurement of parameters using B1500a Parameter Analyzer



The graph output by the parameter analyzer is akin to that displayed on the datasheet, as well as those shown in multiple other classes, where we did labs just like this one for the same results.

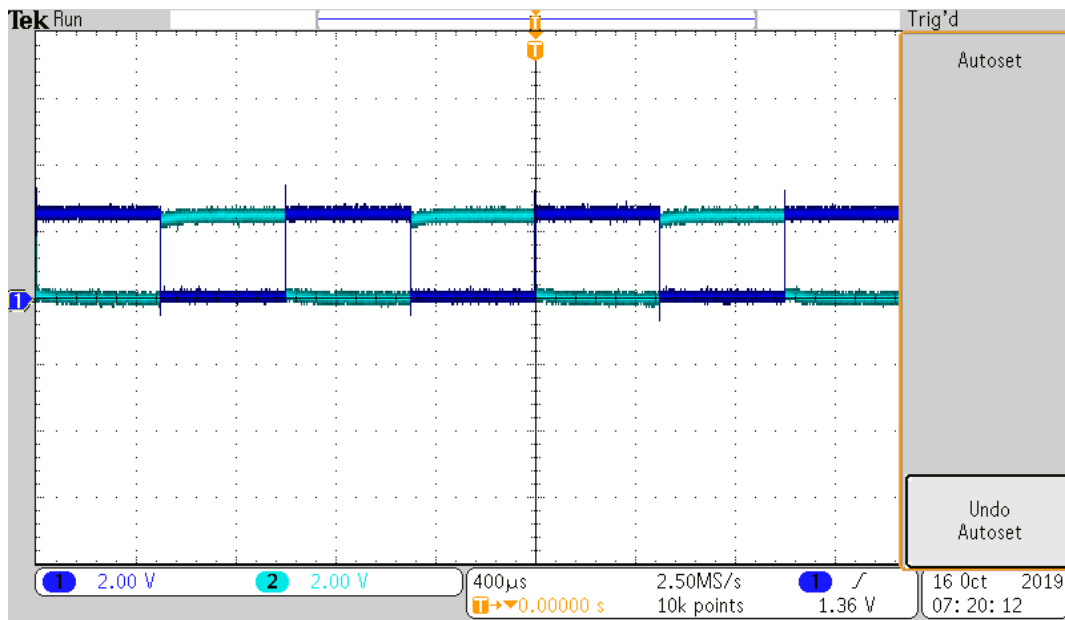
Part 5. CMOS Inverter

Short Channel -

$V_{in} = 0V: V_O = 1.625V$

$V_{in} = 2.5V: V_O = 0.423V$

There appears to be a small delay in the signal as it switches, but otherwise the inverted signal is a near complete match to the input.



Long Channel -

$V_{in} = 0V: V_O = 2.501V$

$V_{in} = 2.5V: V_O = 0.001V$

The delay after a switch is more apparent with these transistors, but the model effectively inverts the input signal with near complete efficiency.

